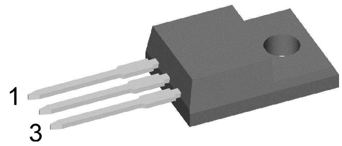
High Efficiency Thyristor

V_{RRM} = 800 V
I_{TAV} = 10 A
V_T = 1.07 V

Single Thyristor

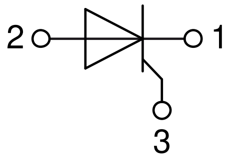
Part number

CLA16E800PN



Backside: isolated

E72873



Features / Advantages:

- Thyristor for line frequency
- Planar passivated chip
- Long-term stability

Applications:

- Line rectifying 50/60 Hz
- Softstart AC motor control
- DC Motor control
- Power converter
- AC power control
- Lighting and temperature control

Package: TO-220FP

- Isolation Voltage: 2500 V~
- Industry standard outline
- RoHS compliant
- Epoxy meets UL 94V-0
- Soldering pins for PCB mounting
- Base plate: Plastic overmolded tab
- Reduced weight

Disclaimer Notice

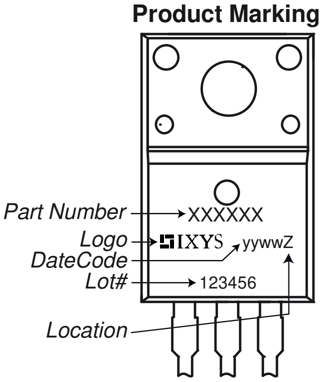
Thyristor

Symbol	Definition	Conditions		min.	typ.	max.	Unit
$V_{RSM/DSM}$	*max. non-repetitive reverse/forward blocking voltage*		T_{VJ} = 25°C			900	V
$V_{RRM/DRM}$	*max. repetitive reverse/forward blocking voltage*		T_{VJ} = 25°C			800	V
$I_{R/D}$	*reverse current, drain current*	$V_{R/D}$ = 800 V	T_{VJ} = 25°C			10	µA
		$V_{R/D}$ = 800 V	T_{VJ} = 125°C			1	mA
V_T	*forward voltage drop*	I_T = 10 A	T_{VJ} = 25°C			1.14	V
		I_T = 20 A				1.32	V
		I_T = 10 A	T_{VJ} = 125°C			1.07	V
		I_T = 20 A				1.31	V
I_{TAV}	*average forward current*	T_C = 90°C	T_{VJ} = 150°C			10	A
$I_{T(RMS)}$	*RMS forward current*	180° sine				16	A
V_{T0}	*threshold voltage*	*for power loss calculation only*	T_{VJ} = 150°C			0.81	V
r_T	*slope resistance*					24	mΩ
R_{thJC}	*thermal resistance junction to case*					4	K/W
R_{thCH}	*thermal resistance case to heatsink*				0.5		K/W
P_{tot}	*total power dissipation*		T_C = 25°C			31	W
I_{TSM}	*max. forward surge current*	t = 10 ms; (50 Hz), sine	T_{VJ} = 45°C			180	A
		t = 8,3 ms; (60 Hz), sine	V_R = 0 V			195	A
		t = 10 ms; (50 Hz), sine	T_{VJ} = 150°C			155	A
		t = 8,3 ms; (60 Hz), sine	V_R = 0 V			165	A
I^2t	*value for fusing*	t = 10 ms; (50 Hz), sine	T_{VJ} = 45°C			160	A²s
		t = 8,3 ms; (60 Hz), sine	V_R = 0 V			160	A²s
		t = 10 ms; (50 Hz), sine	T_{VJ} = 150°C			120	A²s
		t = 8,3 ms; (60 Hz), sine	V_R = 0 V			115	A²s
C_J	*junction capacitance*	V_R = 400 V f = 1 MHz	T_{VJ} = 25°C		7		pF
P_{GM}	*max. gate power dissipation*	t_P = 30 µs	T_C = 150°C			5	W
		t_P = 300 µs				2.55	W
P_{GAV}	*average gate power dissipation*					0.5	W
$(di/dt)_{cr}$	*critical rate of rise of current*	T_{VJ} = 125 °C; f = 50 Hz	repetitive, I_T = 60 A			150	A/µs
		t_P = 200 µs; di_G/dt = 0.3 A/µs;					
		I_G = 0.3 A; V = ⅔ V_{DRM}	non-repet., I_T = 20 A			500	A/µs
$(dv/dt)_{cr}$	*critical rate of rise of voltage*	V = ⅔ V_{DRM}	T_{VJ} = 125°C			500	V/µs
		R_{GK} = ∞; method 1 (linear voltage rise)					
V_{GT}	*gate trigger voltage*	V_D = 6 V	T_{VJ} = 25°C			1.3	V
			T_{VJ} = -40°C			1.6	V
I_{GT}	*gate trigger current*	V_D = 6 V	T_{VJ} = 25°C			30	mA
			T_{VJ} = -40°C			50	mA
V_{GD}	*gate non-trigger voltage*	V_D = ⅔ V_{DRM}	T_{VJ} = 150°C			0.2	V
I_{GD}	*gate non-trigger current*					1	mA
I_L	*latching current*	t_p = 10 µs	T_{VJ} = 25°C			60	mA
		I_G = 0.3 A; di_G/dt = 0.3 A/µs					
I_H	*holding current*	V_D = 6 V R_{GK} = ∞	T_{VJ} = 25°C			60	mA
t_{gd}	*gate controlled delay time*	V_D = ½ V_{DRM}	T_{VJ} = 25°C			2	µs
		I_G = 0.3 A; di_G/dt = 0.3 A/µs					
t_q	*turn-off time*	V_R = 100 V; I_T = 20A; V = ⅔ V_{DRM}	T_{VJ} = 125 °C		150		µs
		di/dt = 10 A/µs dv/dt = 20 V/µs t_p = 200 µs					

IXYS reserves the right to change limits, conditions and dimensions. Data according to IEC 60747and per semiconductor unless otherwise specified 20191129b

Package TO-220FP			Ratings			
Symbol	**Definition**	**Conditions**	**min.**	**typ.**	**max.**	**Unit**
I_{RMS}	*RMS current*	per terminal			35	A
T_{VJ}	*virtual junction temperature*		-55		150	°C
T_{op}	*operation temperature*		-55		125	°C
T_{stg}	*storage temperature*		-55		150	°C
Weight				2		g
M_D	*mounting torque*		0.4		0.6	Nm
F_C	*mounting force with clip*		20		60	N
$d_{Spp/App}$	*creepage distance on surface | striking distance through air*	*terminal to terminal* 1.6	1.0			mm
$d_{Spb/Apb}$		*terminal to backside* 2.5	2.5			mm
V_{ISOL}	*isolation voltage*	t = 1 second; 50/60 Hz, RMS; $I_{ISOL} \le 1$ mA	2500			V
		t = 1 minute	2100			V

Product Marking



Part description

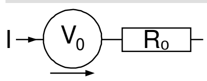
C = Thyristor (SCR)
L = High Efficiency Thyristor
A = (up to 1200V)
16 = Current Rating [A]
E = Single Thyristor
800 = Reverse Voltage [V]
PN = TO-220ABFP (3)

Ordering	Ordering Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standard	CLA16E800PN	CLA16E800PN	Tube	50	517741

Similar Part	Package	Voltage class
CLA16E1200PN	TO-220ABFP (3)	1200
CS22-08io1M	TO-220ABFP (3)	800
CS22-12io1M	TO-220ABFP (3)	1200
CMA30E1600PN	TO-220ABFP (3)	1600

Equivalent Circuits for Simulation

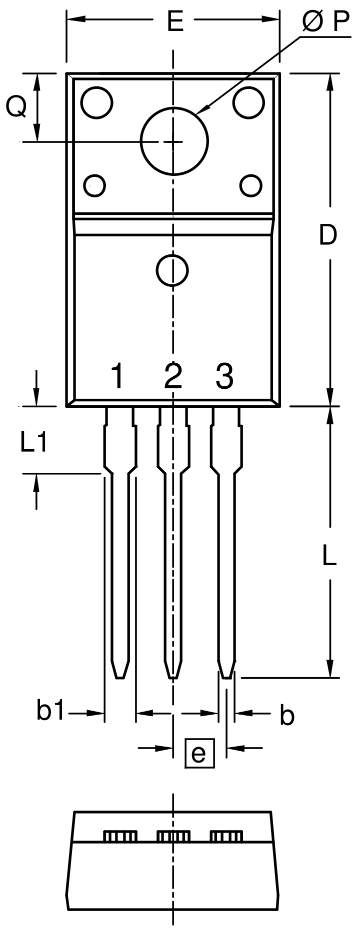
* on die level $T_{VJ} = 150°C$

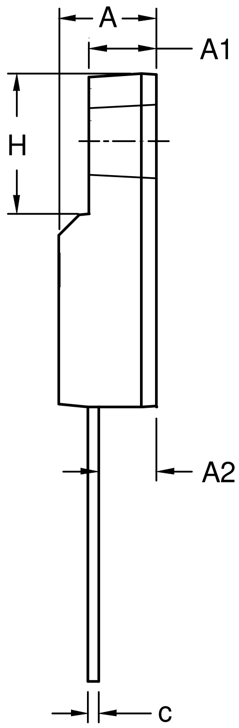


Thyristor

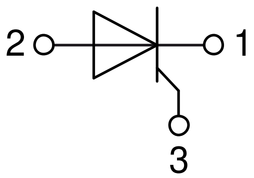
$V_{0\ max}$	*threshold voltage*	0.81	V
$R_{0\ max}$	*slope resistance **	21	mΩ

Outlines TO-220FP





Dim.	Millimeters		Inches	
	min	max	min	max
A	4.50	4.90	0.177	0.193
A1	2.34	2.74	0.092	0.108
A2	2.56	2.96	0.101	0.117
b	0.70	0.90	0.028	0.035
c	0.45	0.60	0.018	0.024
D	15.67	16.07	0.617	0.633
E	9.96	10.36	0.392	0.408
e	2.54 BSC		0.100 BSC	
H	6.48	6.88	0.255	0.271
L	12.68	13.28	0.499	0.523
L1	3.03	3.43	0.119	0.135
Ø P	3.08	3.28	0.121	0.129
Q	3.20	3.40	0.126	0.134



Thyristor

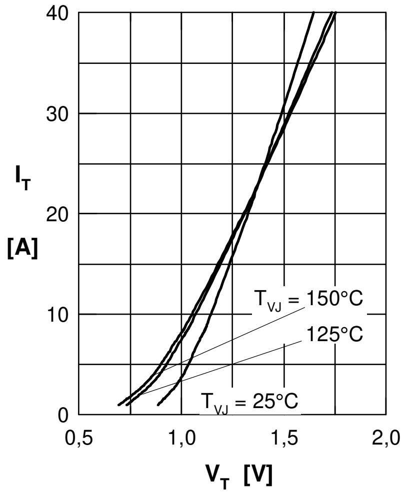


Fig. 1 Forward characteristics

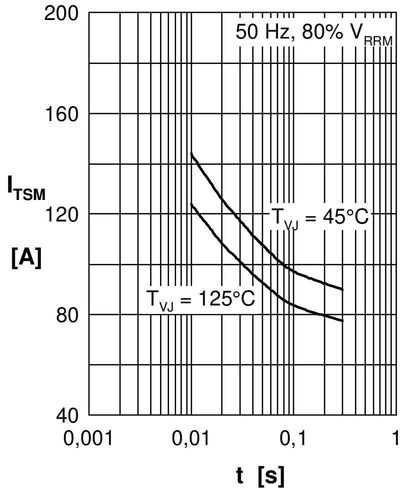


Fig. 2 Surge overload current
I_{TSM}: crest value, t: duration

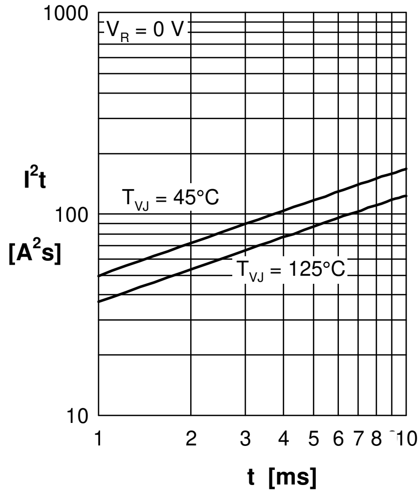


Fig. 3 I^2t versus time (1-10 s)

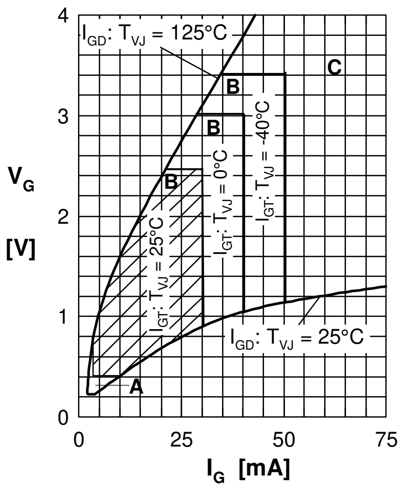


Fig. 4 Gate voltage & gate current
Triggering: A = no; B = possible; C = safe

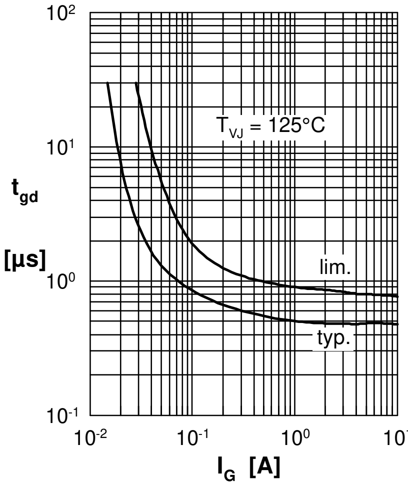


Fig. 5 Gate controlled delay time t_{gd}

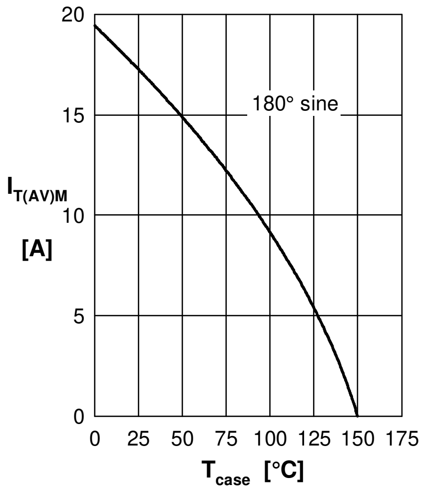


Fig. 6 Max. forward current at case temperature

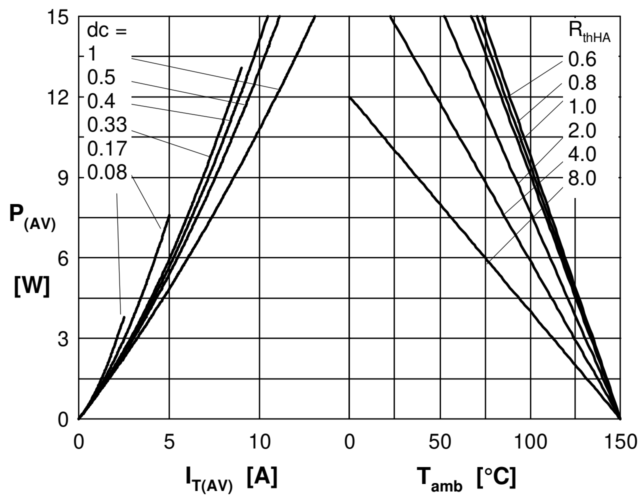
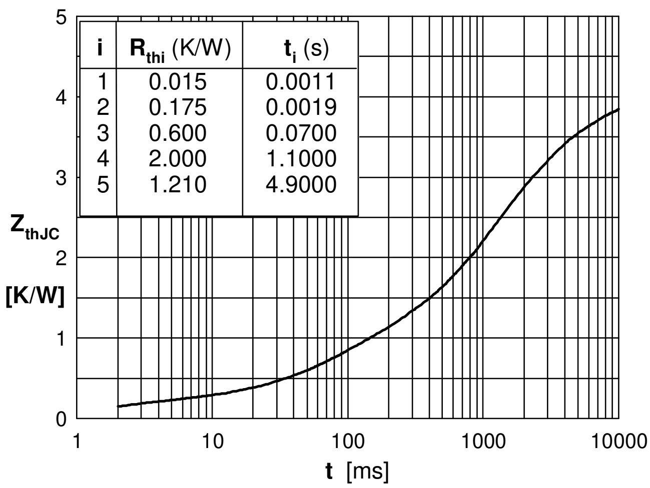


Fig. 7a Power dissipation versus direct output current
Fig. 7b and ambient temperature



i	R_{thi} (K/W)	t_i (s)
1	0.015	0.0011
2	0.175	0.0019
3	0.600	0.0700
4	2.000	1.1000
5	1.210	4.9000

Fig. 8 Transient thermal impedance junction to case